SAMYANG ELECTRONICS

ABS1502 --- ABS1510

SILICON BRIDGE RECTIFIERS

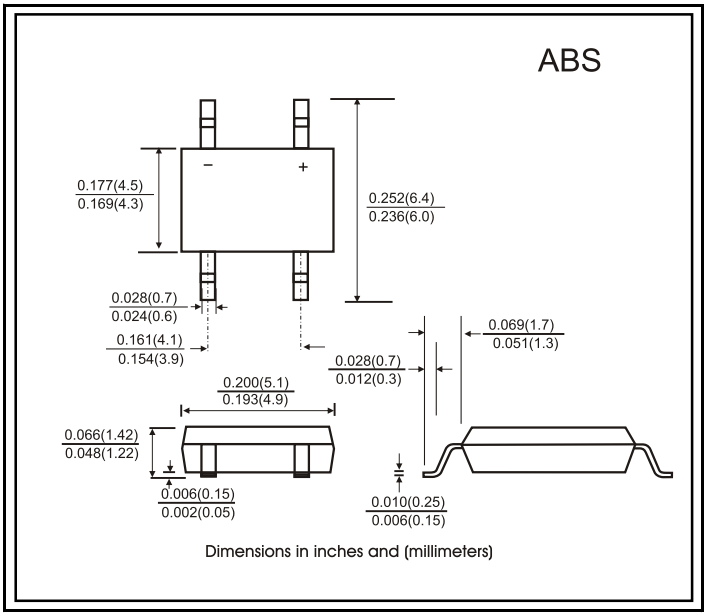
VOLTAGE RANGE: 200 --- 1000 V
CURRENT: 1.5 A

FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Glass passivated chip junction
- Rating to 1000V PRV
- Ideal for printed circuit board
  High temperature soldering guaranteed:260°C/10 seconds at terminals
  Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

MECHANICAL DATA

- *Case*: ABS molded plastic body
- *Epoxy:* UL94V-0 rate flame retardant
- *Terminals*: Plated leads solderable per MIL-STD-750,method 2026
- *Mounting Position*: Any
- *Weight*: 0.0044ounce, 0.125 gram



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

Limiting Values（Absolute Maximum Rating）

Item	Symbol	Unit	Conditions		ABS15				
					02	04	06	08	10
Repetitive Peak Reverse Voltage	V_{RRM}	V			200	400	600	800	1000
Average Rectified Output Current	I_O	A	60Hz sine wave, R-load,Ta=25℃	On alumina substrate	1.5				
Surge(Non-repetitive)Forward Current	I_{FSM}	A	$60H_Z$ sine wave, 1 cycle, T_j=25℃		40				
Current Squared Time	I^2t	A^2S	1ms≤t<8.3ms Tj=25℃， Rating of per diode		6.6				
Storage Temperature	T_{stg}	℃			-55 ~+125				
Junction Temperature	T_j	℃			-55 ~+150				

Electrical Characteristics（T =25℃ Unless otherwise specified）

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	V_{FM}	V	I_{FM}=0.7A, Pulse measurement, Rating of per diode	0.95
Peak Reverse Current	I_{RRM}	μA	V_{RM}=V_{RRM} , Pulse measurement, Rating of per diode	10
Thermal Resistance	$R_{\theta J-A}$	℃/W	Between junction and ambient, On alumina substrate	62.5
	$R_{\theta J-L}$		Between junction and lead	25

FIG1:Maximum Forward Current Derating Carve

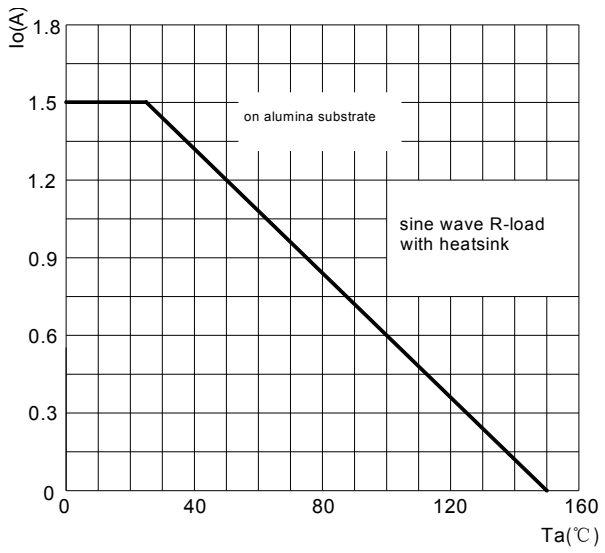


FIG2:Surge Forward Current Capadility

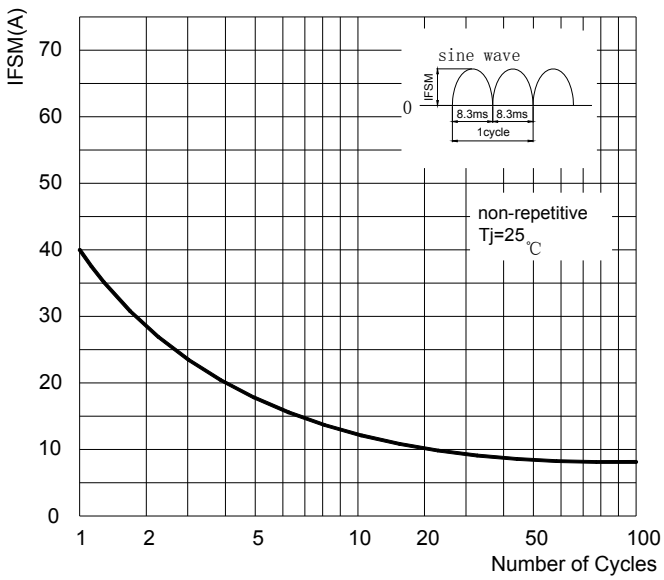


FIG3: Forward Voltage

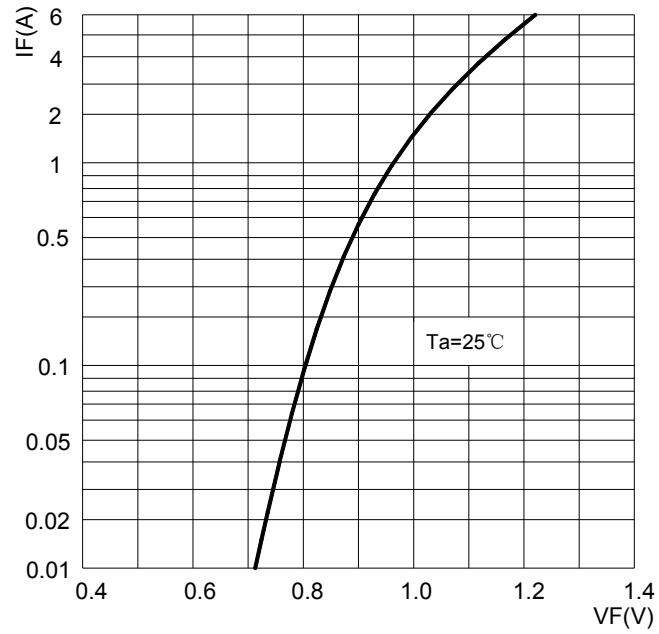


FIG4:Typical Reverse Characteristics

